G2N5551

NPN EPITAXIAL PLANAR TRANSISTOR

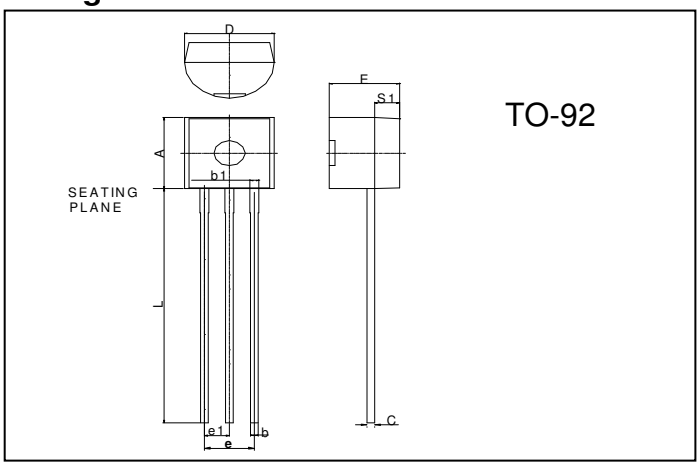
Description

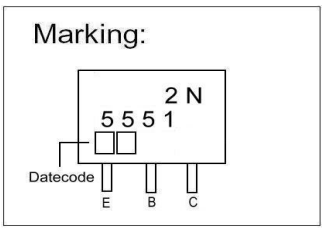
The G2N5551 is designed for general purpose switching and amplifier applications.

Features

*Complementary to PNP Type G2N5401
*High Collector – Emitter Breakdown Voltage (V_{CEO} > 160V (@I_C=1mA)

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S_1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b_1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage	V_{CBO}	180	V
Collector to Emitter Voltage	V_{CEO}	160	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current	I_C	600	mA
Total Power Dissipation	P_D	625	mW

Characteristics at Ta = 25℃

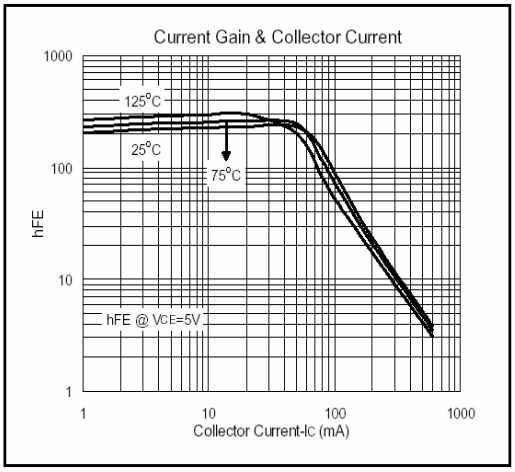
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	180	-	-	V	I_C=100uA , I_E=0
BV_{CEO}	160	-	-	V	I_C=1mA,I_B=0
BV_{EBO}	6	-	-	V	I_E=10uA ,I_C=0
I_{CBO}	-	-	50	nA	V_{CB}=120V, I_E=0
I_{EBO}	-	-	50	nA	V_{EB}=4V, I_C=0
*V_{CE}(sat)1	-	-	0.15	V	I_C=10mA, I_B=1mA
*V_{CE}(sat)2	-	-	0.2	V	I_C=50mA, I_B=5mA
*V_{BE}(sat)1	-	-	1	V	I_C=10mA, I_B=1mA
*V_{BE}(sat)2	-	-	1	V	I_C=50mA, I_B=5mA
*hFE1	80	-	-		V_{CE}=5V, I_C=1mA
*hFE2	80	160	400		V_{CE}=5V, I_C=10mA
*hFE3	50	-	-		V_{CE}=5V, I_C=50mA
fT	100		300	MHz	V_{CE}=10V, I_C=10mA, f=100MHz
Cob	-	-	6	pF	V_{CB}=10V, f=1MHz, I_E=0

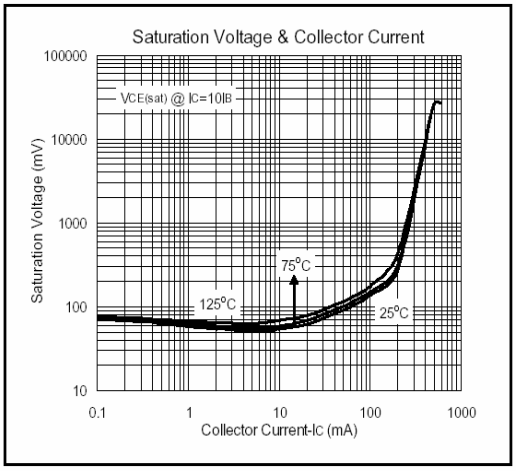
* Pulse Test: Pulse Width≦380us, Duty Cycle≦2%

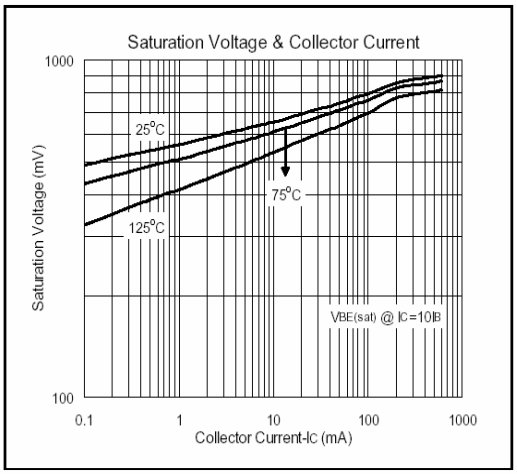
Classification OF h_{FE2}

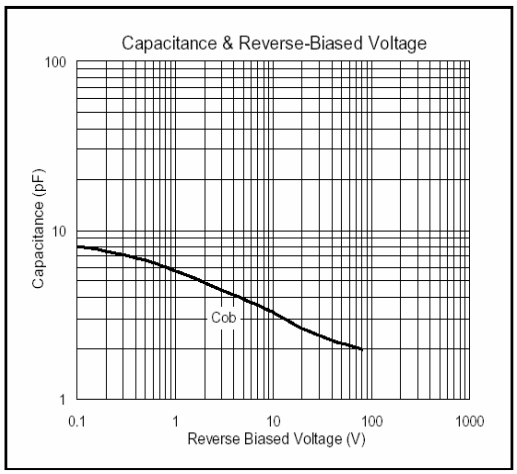
Rank	A	N	C
Range	80-200	100-250	160-400

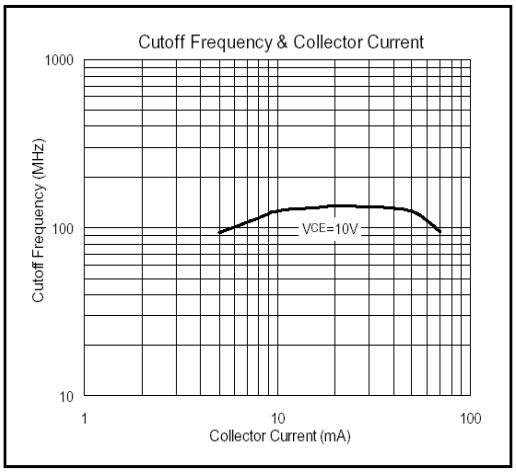
Characteristics Curve

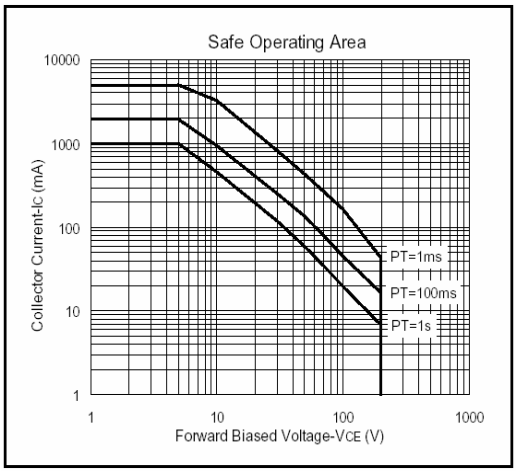


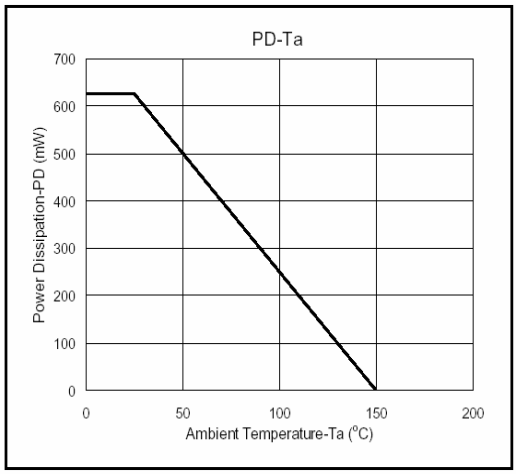












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